

# On the Enlargement of Single Event Transients' Width in Flash-based FPGAs

***Authors:*** N. Battezzati, L. Sterpone, M. Violante (*Politecnico di Torino*), S. Gerardin, A. Manuzzato, A. Paccagnella (*Università di Padova*), S. Rezgui (*Actel Corp.*), D. Merodio, R. Sorensen, C. Poivey (*ESA*)

*MAPLD 2008*



# Outline

- The goals of this work
- Background
- The proposed methodology
- A case study
- Experimental results
- Conclusions and future works

# The goals of the work

- Analysis of the robustness of designs implemented in Flash-based FPGAs
- Study of transient faults effects in safety- and mission-critical designs



# Flash-based FPGAs

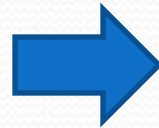
- FPGAs capable of in-the-field modifications to the configuration of:
  - Programmable logic blocks (VersaTiles)
  - Programmable interconnections
- The configuration memory is manufactured using the Flash memory technology.

# Radiation effects in Flash-based FPGAs

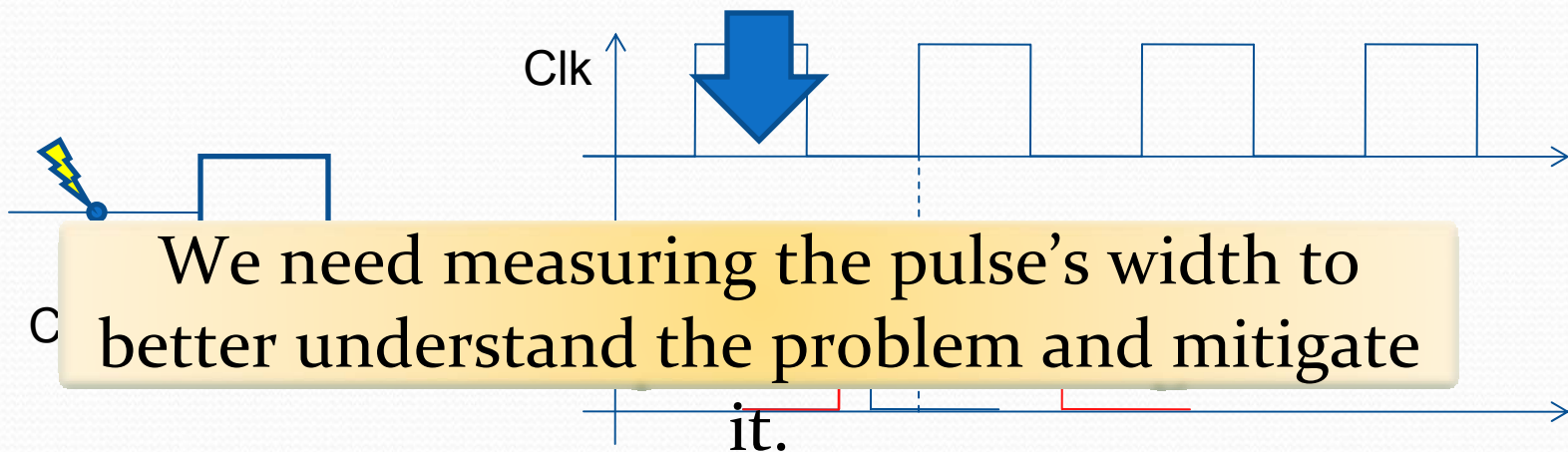
- Configuration memory of Flash-based FPGAs cannot be upset, because of the technology and the cell size
- Single Event Transients (SETs) become more relevant.

# Transient effects

- The effect of an SET is mainly due to:
  - Location
  - Arrival time
  - Pulse's width.



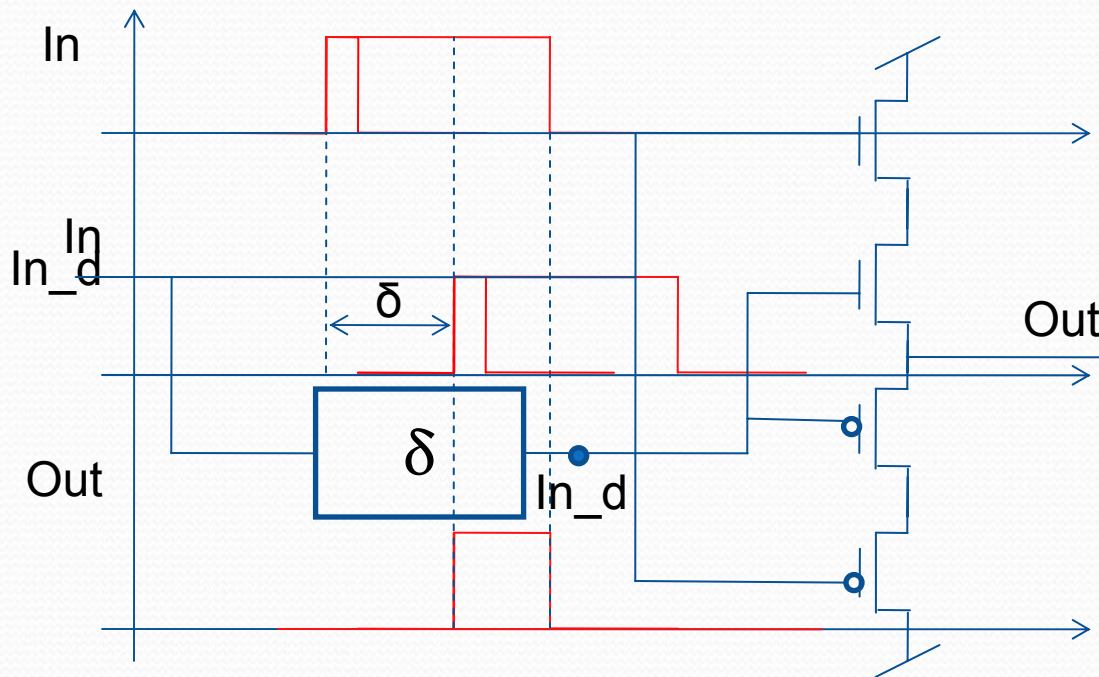
Infinite number of combinations



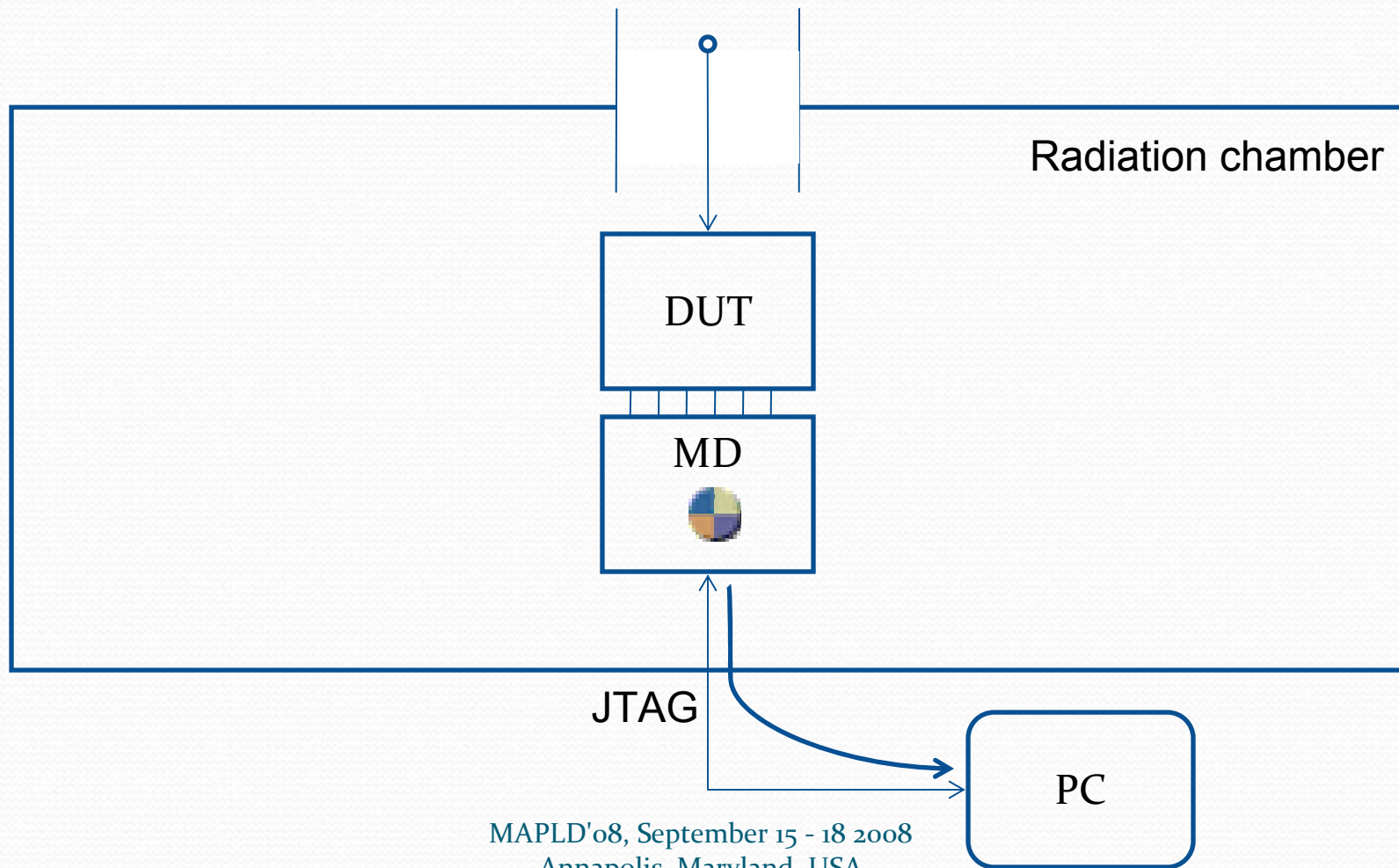


# Background

- Guard gate mitigation technique



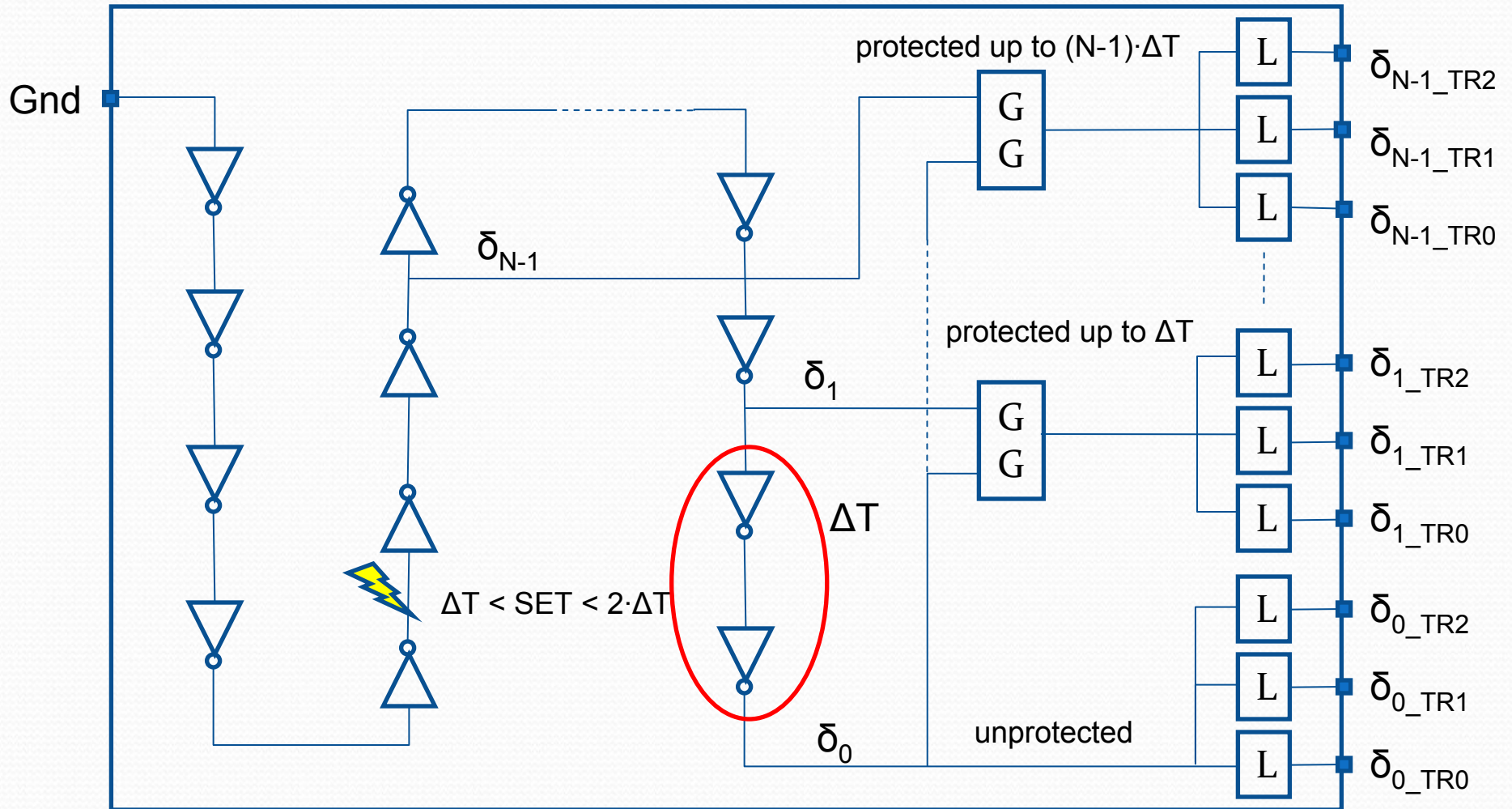
# The proposed methodology



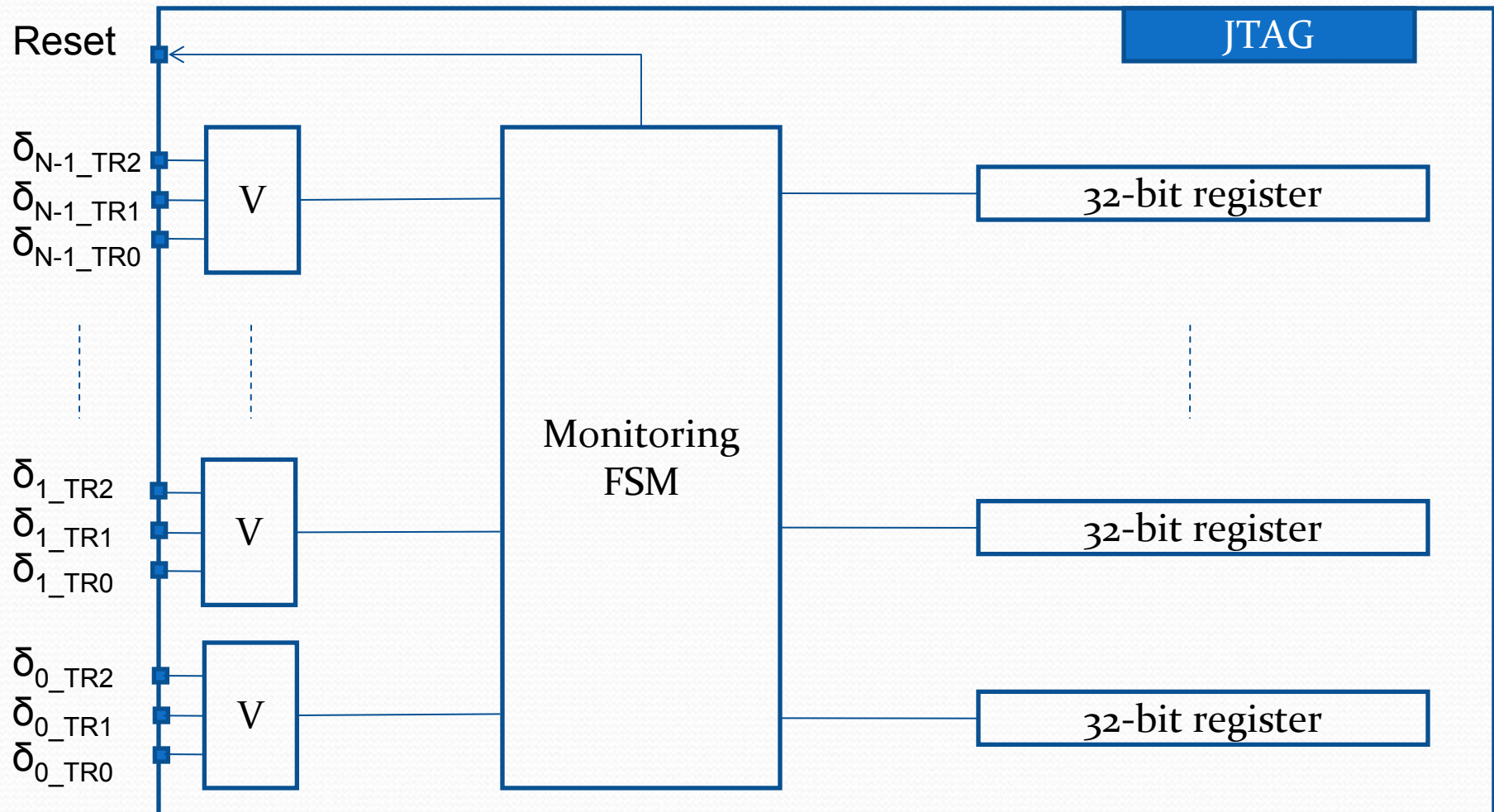
MAPLD'o8, September 15 - 18 2008  
Annapolis, Maryland, USA



# The DUT Design



# The Monitoring Design



# Design challenges

- Different I/O banks
- Blind time
- Design cross-section
- Number of voted channels,  $\delta_0 \dots \delta_{N-1}$

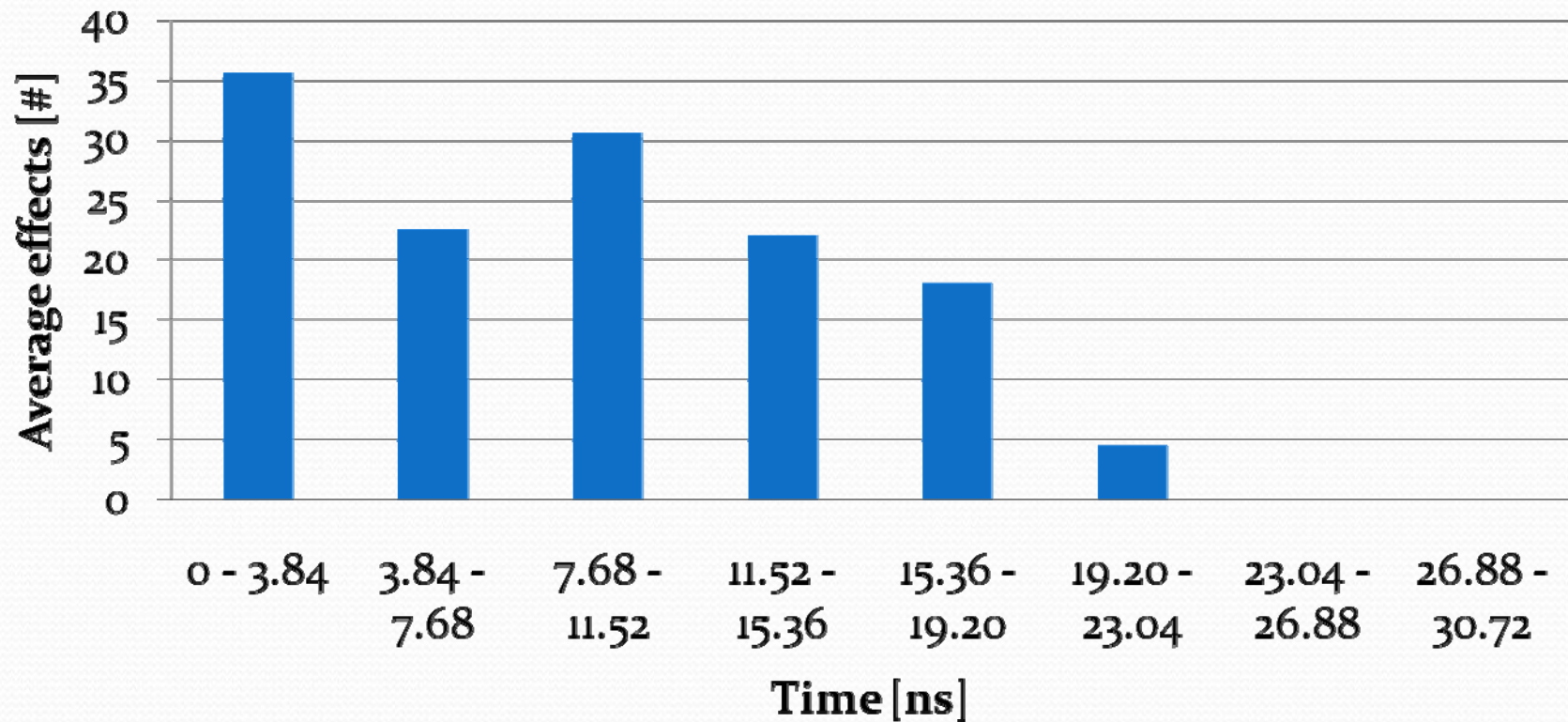


# A case study

- DUT: Actel ProASIC3 250
  - 6,144 VersaTiles
  - A single chain composed of 5,652 inverters (> 90% VersaTiles)
  - 9 channels,  $\Delta T = 0.96$  ns
- MD: Xilinx Virtex-II Pro 4
  - 100 MHz clock  $\rightarrow$  blind time  $\approx 20$  ns
  - Partial readback capability
  - Full support for 1149.1 IEEE standard (Boundary Scan)
- Ion beams: Louvain-la-Neuve, Belgium
  - Xe ions, LET = 55.9 MeV $\cdot$ cm<sup>2</sup>/mg, different fluences

# Experimental results

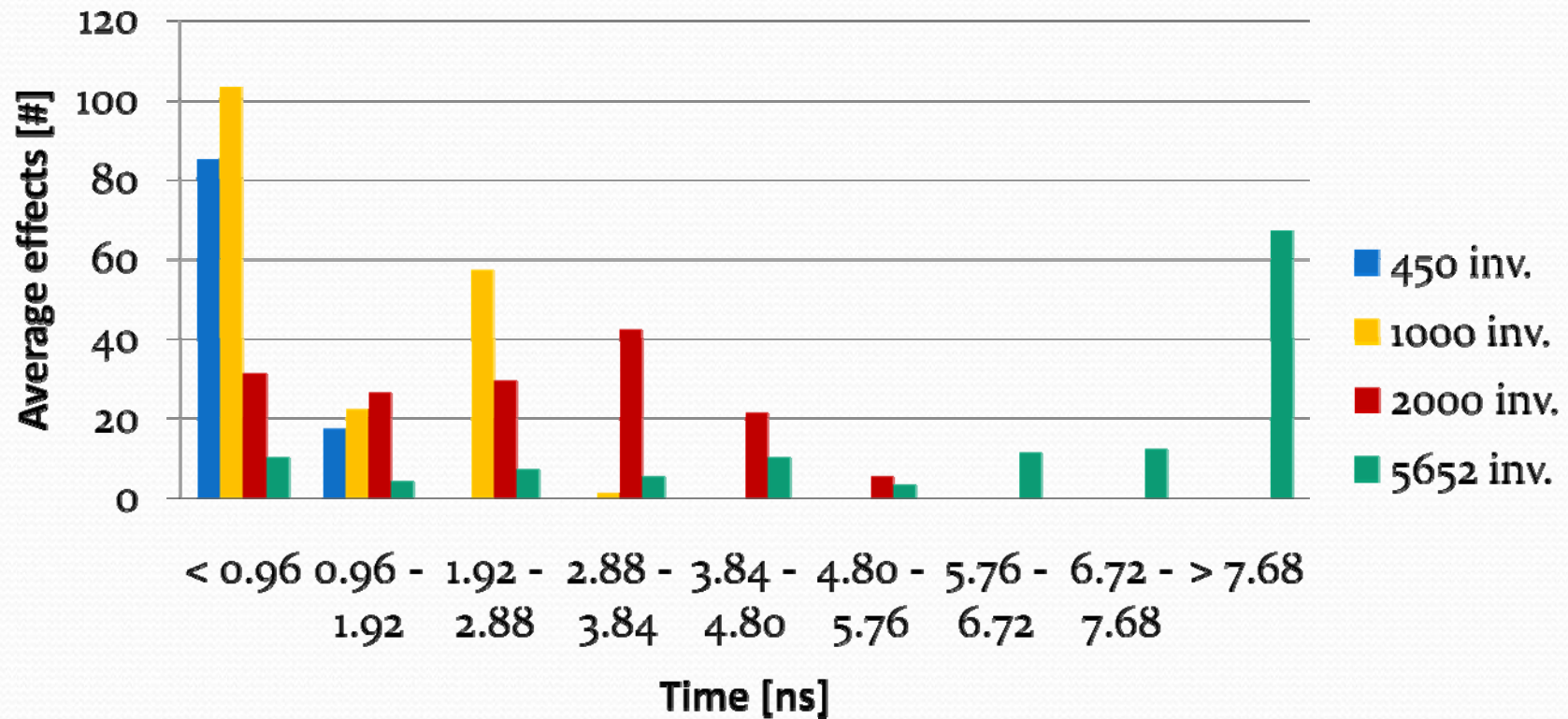
## Observed effects for 5652 inverters chain



MAPLD'o8, September 15 - 18 2008  
Annapolis, Maryland, USA

# Experimental results

## Observed effects wrt different chain lengths





# Conclusions

- We developed a method for evaluating SETs' effects width
  - Independently from the Device Under Test
  - With a very low cost
- The method has been validated comparing it against Actel Corporation's results.

# Future works

- Evaluation of transient effects in *real* designs
  - Investigation of the actual impact of SETs wrt SEUs in real designs
  - Investigation of SETS effects wrt different placement schemes
- Evaluation of hardening techniques effectiveness in real designs
- Development of an *automatic tool* for analyzing and hardening designs implemented in Flash-based FPGAs.



Thank you for your attention

MAPLD'o8, September 15 - 18 2008  
Annapolis, Maryland, USA